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Applicati n Number 09/945,507

Filling Date August 30, 2001

First Named Inventor Forbes, Leonard

Group Art Unit 2824

Examiner Name Dinh, Son

Attorney Docket No: 1303.014US1

Sheet 1 of 3

NFORMATION DISCLOSURE

STATEMENT BY APPLICAN

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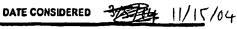
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Dinh, Son

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